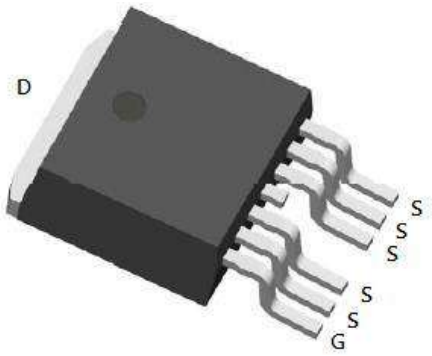
N-Channel Enhancement Mode Power MOSFET

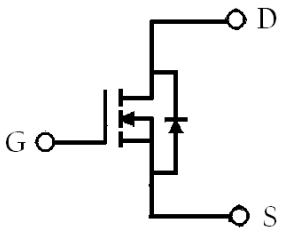
Features:

- Simple Drive Requirement
- Fast Switching Characteristic
- RoHS compliant package

TO-263-7L-4C



BV_{DSS}	80V
I_D @V_{GS}=10V, T_C=25°C	172A
$R_{DSON(TYP)}$ @ V_{GS}=10V, I_D=20A	2.7mΩ



G：Gate D：Drain S：Source

Ordering Information

Device	Package	Shipping
KWE05N08	TO-263-7L-4C (Pb-free lead plating and RoHS compliant package)	800 pcs / Tape & Reel

Absolute Maximum Ratings (TC=25°C, unless otherwise noted)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	±30	
Continuous Drain Current @ TC=25°C(silicon limit)		I_D	202	A
Continuous Drain Current @ TC=100°C(silicon limit)			143	
Continuous Drain Current @ TC=25°C(package limit)	(Note 1)		172	
Pulsed Drain Current	(Note 3)	I_{DM}	688	
Continuous Drain Current @ TA=25°C	(Note 2)	I_{DSM}	16.5	
Continuous Drain Current @ TA=70°C	(Note 2)		13.2	
Avalanche Current @L=0.1mH	(Note 3)	I_{AS}	80	
Avalanche Energy @ L=1mH, ID=60A, VDD=50V	(Note 4)	E_{AS}	1800	mJ
Power Dissipation	TC=25°C (Note 1)	P_D	330	W
	TC=100°C (Note 1)		165	
Power Dissipation	TA=25°C (Note 2)	P_{DSM}	2	
	TA=70°C (Note 2)		1.3	
Operating Junction and Storage Temperature		Tj, Tstg	-55~+175	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{\theta JC}$	0.45	°C/W
Thermal Resistance, Junction-to-ambient, max, (Note 2)	$R_{\theta JA}$	62.5	

Note : 1.The power dissipation P_D is based on $T_{J(MAX)}$=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

2.The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

3. Pulse width limited by junction temperature $T_{J(MAX)}$=175°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

4. 100% tested by conditions of L=1mH, I_{AS}=20A, V_{GS}=15V, V_{DD}=50V.

5. The static characteristics are obtained using <300μs pulses, duty cycle 0.5% maximum.

6. The $R_{\theta JA}$ is the sum of thermal resistance from junction to case $R_{\theta JC}$ and case to ambient.

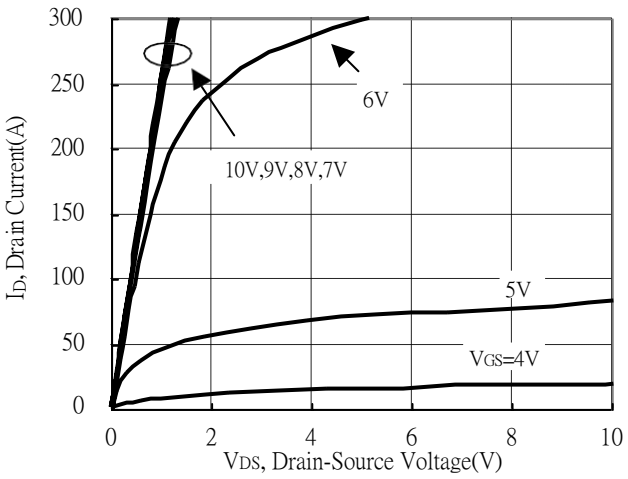
Characteristics (T_C=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	80	-	-	V	V_{GS}=0V, I_D=250μA
$V_{GS(th)}$	2.0	-	4.0		V_{DS} = V_{GS}, I_D=250μA
G_{FS}	-	42.8	-	S	V_{DS} =10V, I_D=20A
I_{GSS}	-	-	±100	nA	V_{GS}=±30V
I_{DSS}	-	-	1	μA	V_{DS} =64V, V_{GS} =0V
	-	-	25		V_{DS} =64V, V_{GS} =0V, Tj=125°C
*$R_{DS(ON)}$	-	2.7	3.8	mΩ	V_{GS} =10V, I_D=20A
Dynamic					
*Qg	-	123.8	-	nC	I_D=20A, V_{DS}=40V, V_{GS}=10V
*Qgs	-	21	-		
*Qgd	-	44.8	-		
*$t_{d(ON)}$	-	41	-	ns	V_{DS}=40V, I_D=20A, V_{GS}=10V, R_G=1Ω
*tr	-	35.6	-		
*$t_{d(OFF)}$	-	90	-		
*t_f	-	23.2	-		
Ciss	-	5776	-	pF	V_{GS}=0V, V_{DS}=40V, f=1MHz
Coss	-	638	-		
Crss	-	213	-		
Rg	-	1.6	-	Ω	f=1MHz
Source-Drain Diode					
*I_S	-	-	172	A	
*I_{SM}	-	-	688		
*V_{SD}	-	0.66	1	V	I_S=1A, V_{GS}=0V
*trr	-	44.2	-	ns	I_F=1A, V_{GS}=0V, dI_F/dt=100A/μs
*Qrr	-	63.3	-	nC	

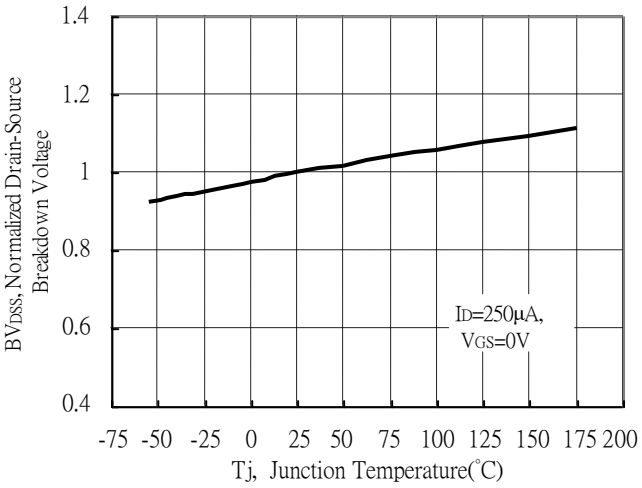
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Typical Characteristics

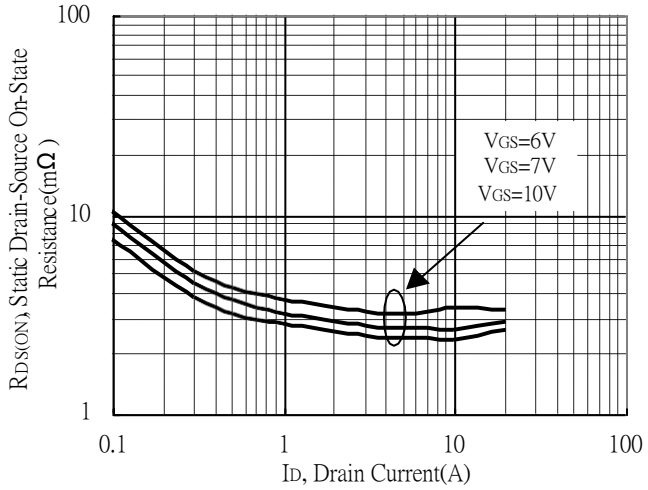
Typical Output Characteristics



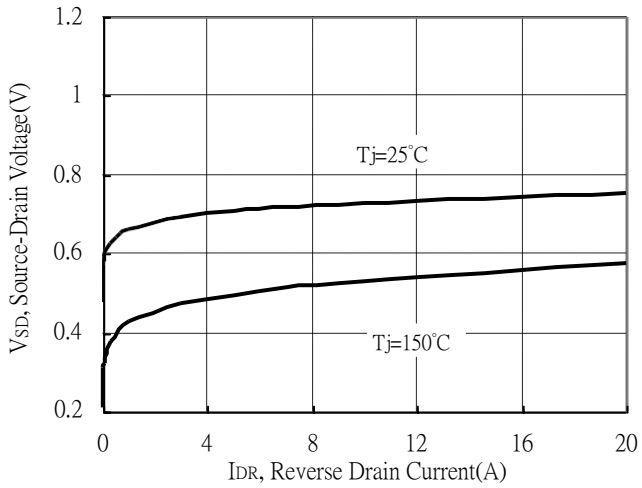
Brekdown Voltage vs Junction Temperature



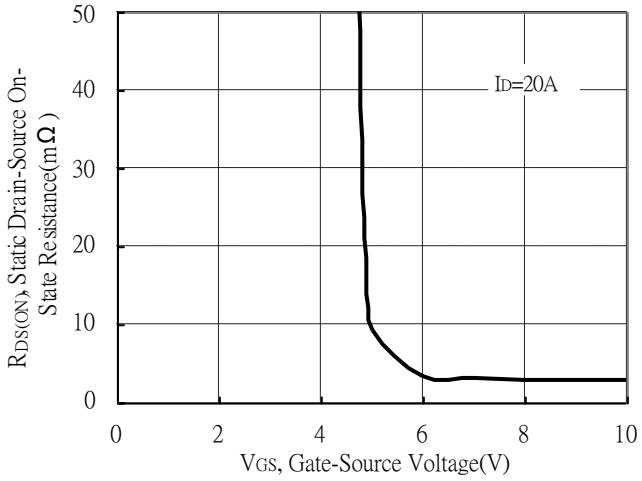
Static Drain-Source On-State resistance vs Drain Current



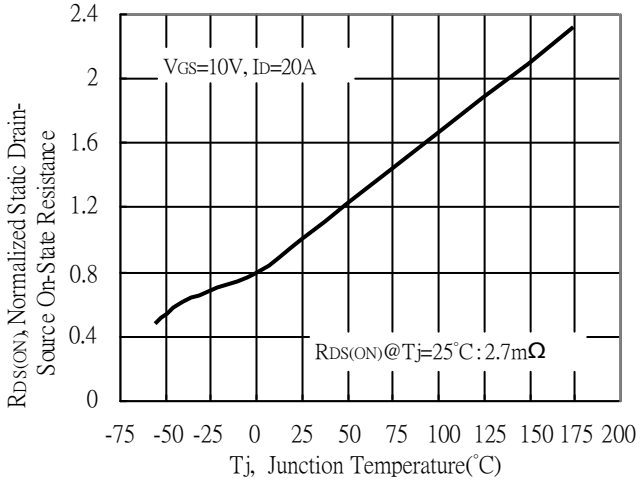
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

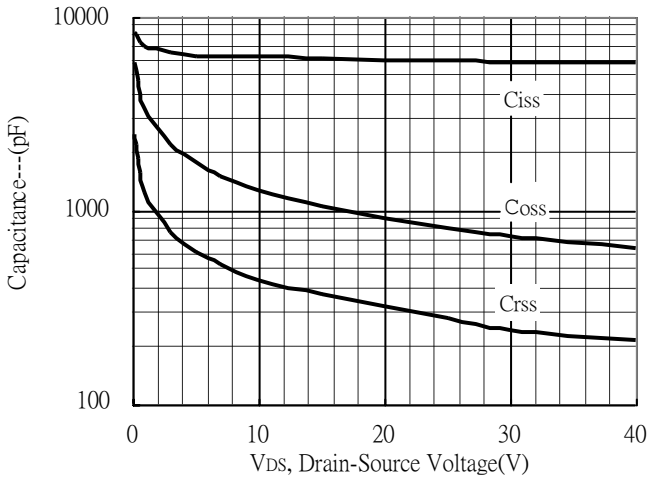


Drain-Source On-State Resistance vs Junction Tempearture

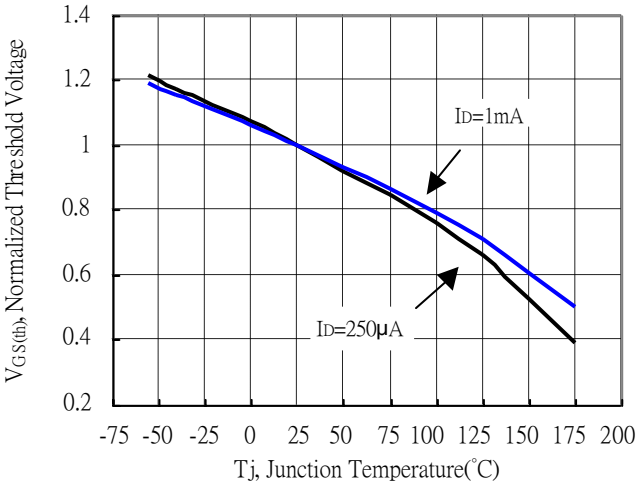


Typical Characteristics(Cont.)

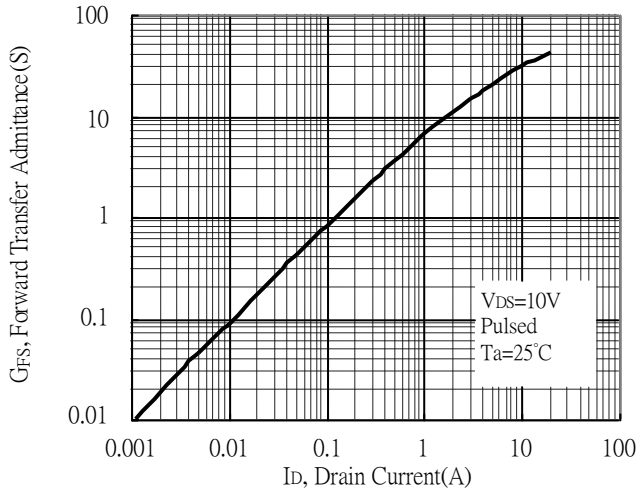
Capacitance vs Drain-to-Source Voltage



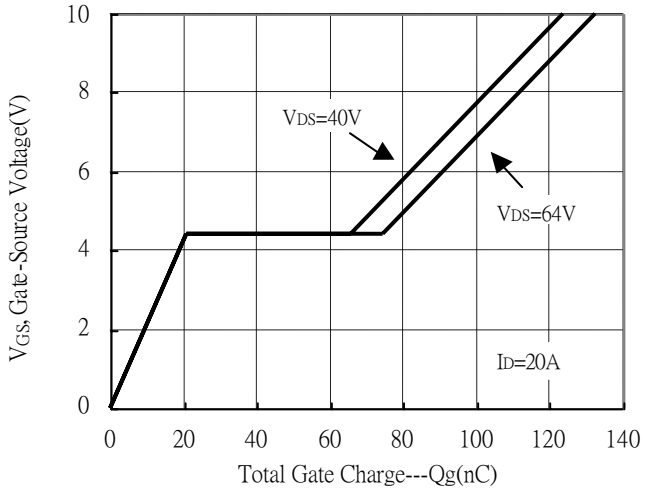
Threshold Voltage vs Junction Tempearture



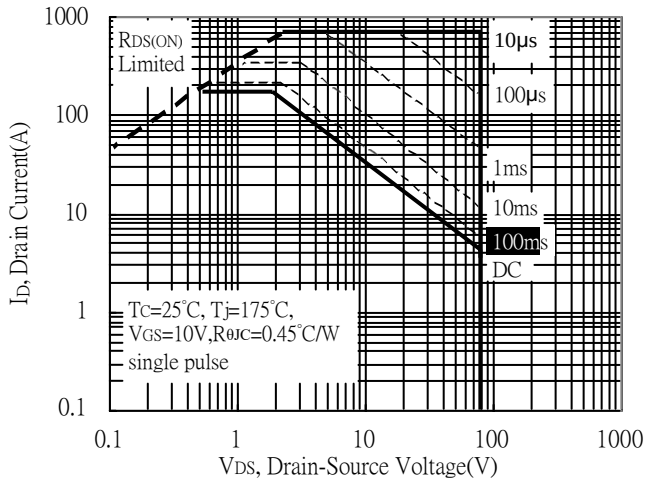
Forward Transfer Admittance vs Drain Current



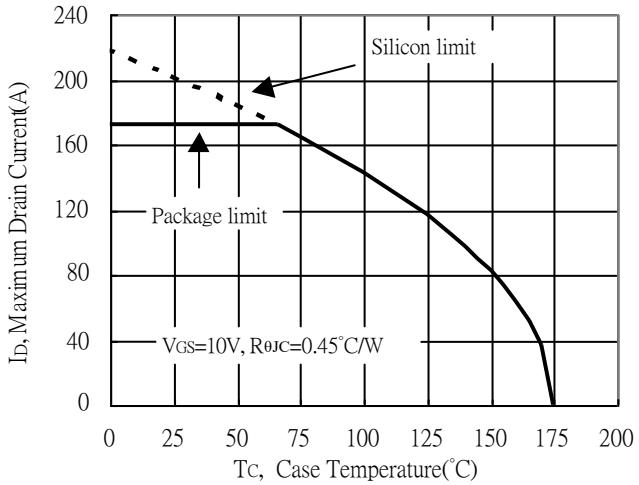
Gate Charge Characteristics



Maximum Safe Operating Area

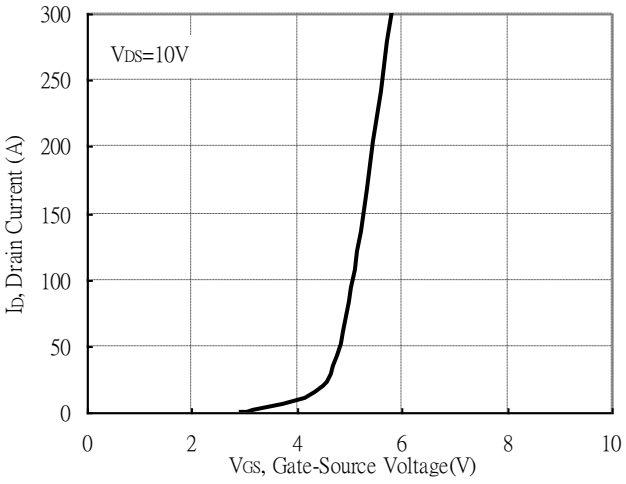


Maximum Drain Current vs Case Temperature

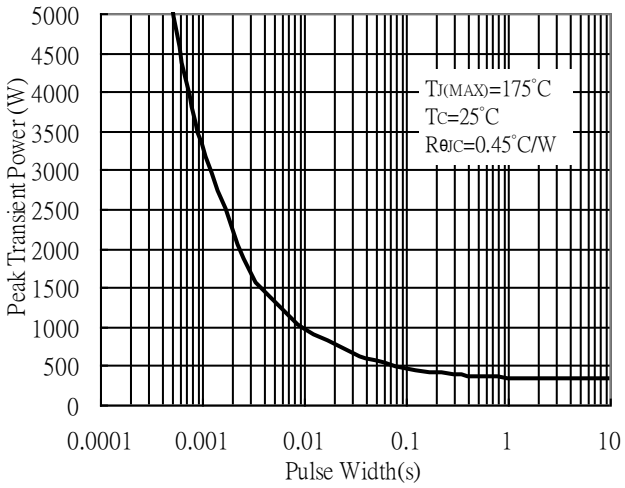


Typical Characteristics(Cont.)

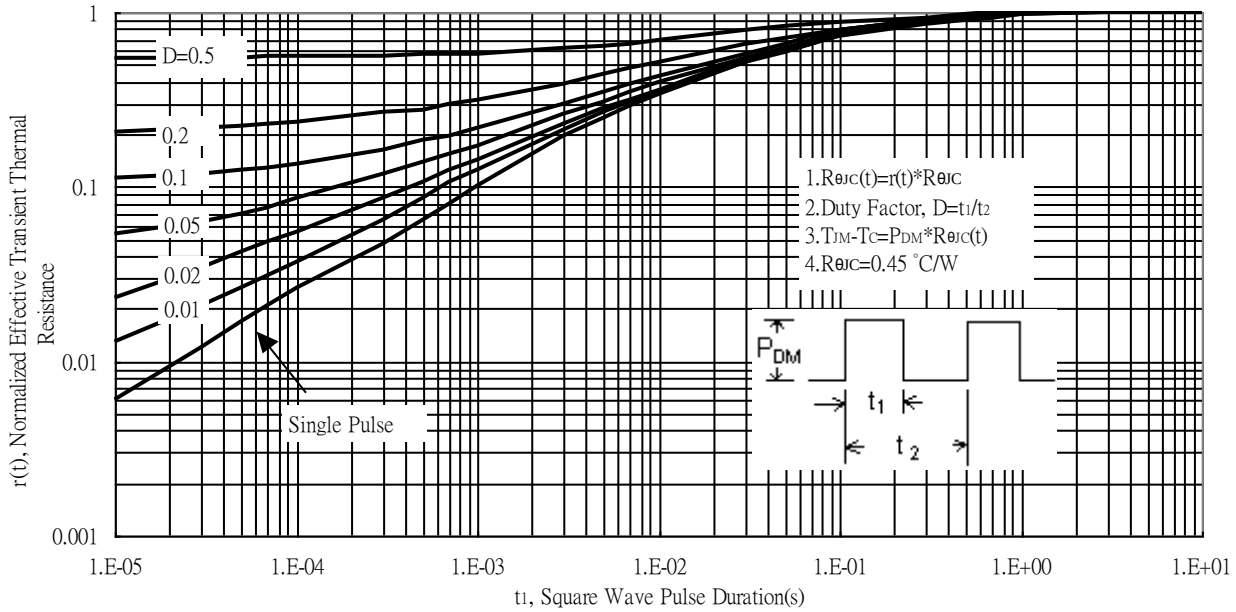
Typical Transfer Characteristics



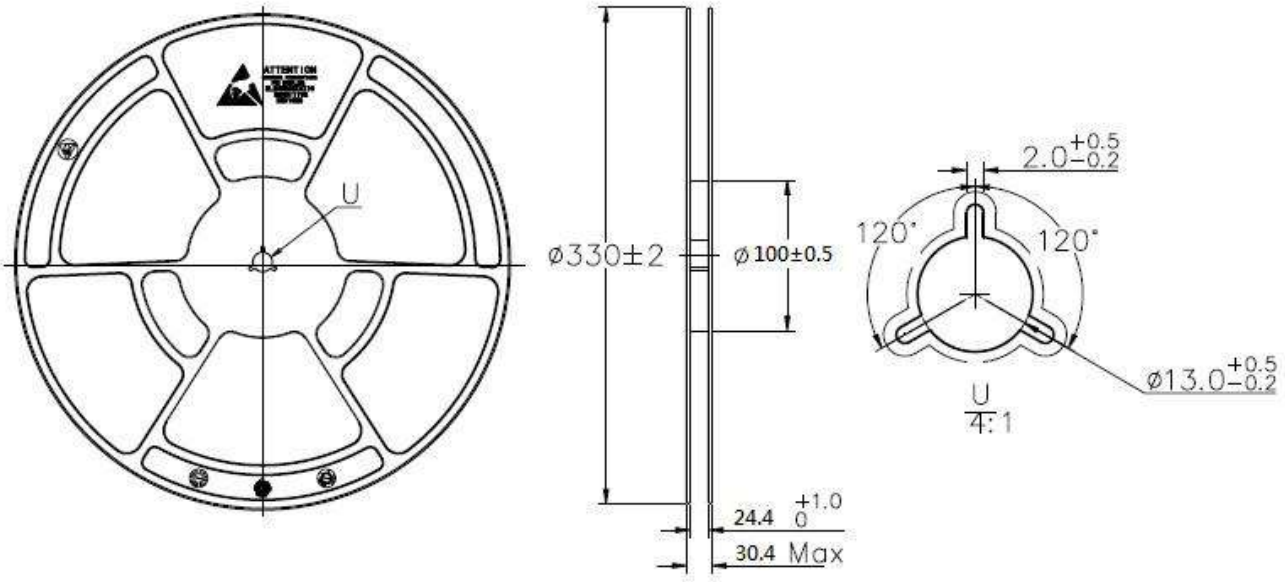
Single Pulse Maximum Power Dissipation



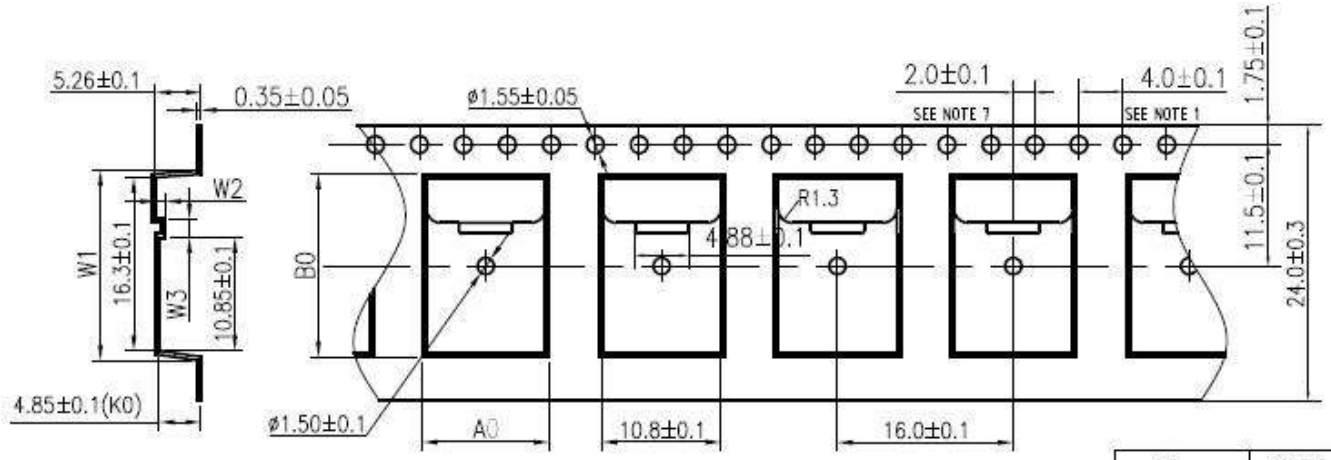
Transient Thermal Response Curves



Reel Dimension



Carrier Tape Dimension

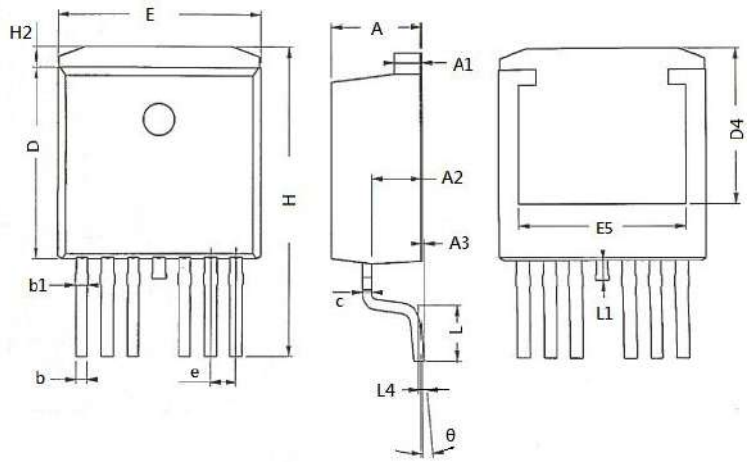


NOTES

1. 10 SPROCKET HOLE PITCH CUMULATIVE TOLEANCE±0.2mm;
2. MATERIAL: BLACK CONDUCTIVE POLYSTYRENE;
3. DEMENSIONS ARE IN mm (UNLESS OTHERWISE SPECIFIEED);
4. K0 MEASURED FROM A PLANE ON THE INSIDE BOTTOM OF THE POCKET TO THE TOP SURFACE ON THE CARRIER;
5. A0 AND B0 MEASURED ON A PLANE 0.30mm ABOVE THE BOTTOM OF THE POCKET;
6. SURFACE RESISTIVITY IS BETWEEN 1×10E6 TO 1×10E10 OHMS/SQUARE;
7. Allowable Camber to be 1 mm/100 mm

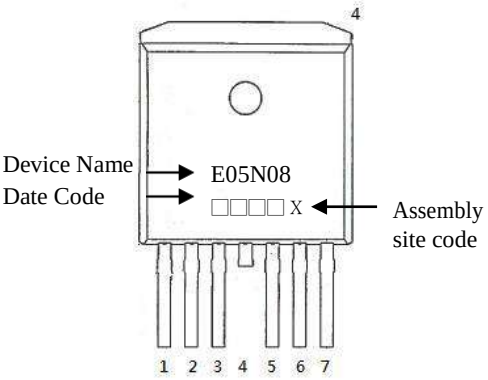
Dim		Spec
opt 1	W1	16.9±0.1
	W2	1.3±0.1
	W3	1.0±0.1
opt 2	W1	17.2±0.1
	W2	1.8±0.1
	W3	0.85±0.1

TO-263-7L-4C Dimension



7-Lead Plastic Surface Mounted TO-263-7L Package

Marking :



Style : Pin 1. Gate
Pin 2, 3, 5, 6, 7 : Source
Pin 4. Drain

Date Code : (From left to right)
First Code : Year code, the last digit of Christinr year. For example, 2014→4, 2015→, 2016→6, …, etc.
Second Code : Month code, Jan→A, Feb→B, Mar→C, Apr→D, May→E, Jun→F, Jul→G, Aug→H, Sep→J, Oct→K, Nov→L, Dec→M
Third and fourth codes : production serial number, 01~99

*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1673	0.1791	4.25	4.55	E	0.3858	0.4016	9.80	10.20
A1	0.0472	0.0551	1.20	1.40	e	0.0500 BSC		1.27 BSC	
A2	0.0886	0.1004	2.25	2.55	E5	0.2854	-	7.25	-
A3	0.0004	0.0098	0.01	0.25	H	0.5768	0.6043	14.65	15.35
b	0.0197	0.0276	0.50	0.70	H2	0.0315	0.0472	0.80	1.20
b1	0.0228	0.0331	0.58	0.84	L	0.0945	0.1181	2.40	3.00
c	0.0157	0.0236	0.40	0.60	L1	0.0335	0.0453	0.85	1.15
D	0.3563	0.3720	9.05	9.45	L4	0.0098 BSC		0.25 BSC	
D4	0.2717	-	6.90	-	θ	2°	8°	2°	8°